



(51) International Patent Classification:

C09G 1/02 (2006.01) *H01L 21/306* (2006.01)
B24B 37/04 (2012.01) *H01L 21/02* (2006.01)

(21) International Application Number:

PCT/EP2014/060802

(22) International Filing Date:

26 May 2014 (26.05.2014)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

13170661.6 5 June 2013 (05.06.2013) EP

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY,

BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, JP, KE, KG, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

— with international search report (Art. 21(3))

(54) Title: A CHEMICAL MECHANICAL POLISHING (CMP) COMPOSITION

(57) Abstract: Use of a chemical mechanical polishing (CMP) composition (Q) for chemical mechanical polishing of a substrate (S) comprising (i) elemental germanium or (ii) $\text{Si}_{1-x}\text{Ge}_x$ with $0.1 \leq x < 1$, wherein the CMP composition (Q) consists essentially of (A) aluminum particles in an amount of from 0.01 to 3 wt.% based on the total weight of the CMP composition (B) at least one oxidizer, (M) an aqueous medium and (N) optionally at least one pH adjusting agent wherein the CMP composition (Q) has a pH of from 2 to 6.

